SHANGHAI SUNRISE ELECTRONICS CO., LTD.

SF1A THRU SF1G SURFACE MOUNT SUPER FAST SWITCHING RECTIFIER VOLTAGE: 50 TO 400V CURRENT: 1.0A

TECHNICAL SPECIFICATION

FEATURS

- Ideal for surface mount pick and
- place application
- Low profile package
- Built-in strain relief
- High surge capability
- Open junction chip,silastic passivated
- Super fast recovery for high efficiency
- High temperature soldering guaranteed: 260°C/10sec/at terminal

MECHANICAL DATA

- Terminal: Plated leads solderable per MIL-STD 202E, method 208C
- Case: Molded with UL-94 Class V-O
 - recognized flame retardant epoxy
- Polarity: Color band denotes cathode

DSMA/DO-214AC В С D F G _ H Е B .177(4.50) .157(3.99) D .012(0.305) <u>.110(2.79)</u> .100(2.54) MAX. .075(1.90) MIN. .052(1.32) .006(0.152 E F G H I MAX. .208(5.28) .090(2.29) .008(0.203) .060(1.52) .035(0.88) .078(1.98) .004(0.102) .030(0.76) .027(0.68) MIN. .194(4.93) Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(Single-phase, half-wave, 60HZ, resistive or inductive load rating at 25°C, unless otherwise stated, for capacitive load, derate current by 20%)

| RATINGS | SYMBOL | SF1A | SF1B | SF1C | SF1D | SF1E | SF1G | UNITS |
|--|---------------------|-------------|------|------|------|------|------|----------|
| Maximum Repetitive Peak Reverse Voltage | V _{RRM} | 50 | 100 | 150 | 200 | 300 | 400 | V |
| Maximum RMS Voltage | V _{RMS} | 35 | 70 | 105 | 140 | 210 | 280 | V |
| Maximum DC Blocking Voltage | V _{DC} | 50 | 100 | 150 | 200 | 300 | 400 | V |
| Maximum Average Forward Rectified Current (T _L =110°C) | I _{F(AV)} | 1.0 | | | | | | А |
| Peak Forward Surge Current (8.3ms single half sine-wave superimposed on rated load) | I _{FSM} | 30 | | | | | | А |
| Maximum Instantaneous Forward Voltage (at rated forward current) | V_{F} | 0.95 1.25 | | | | V | | |
| Maximum DC Reverse Current $T_a=25^{\circ}C$ (at rated DC blocking voltage) $T_a=100^{\circ}C$ | | 5.0 200 | | | | | | μΑ μΑ |
| Maximum Reverse Recovery Time (Note 1) | trr | 35 | | | | | | nS |
| Typical Junction Capacitance (Note 2) | CJ | 10 | | | | | | pF |
| Typical Thermal RSFistance (Note 3) | R _θ (ja) | 40 | | | | | | °C/W |
| Storage and Operation Junction Temperature | T_{STG}, T_{J} | -50 to +150 | | | | | | °C |
| Note: | | | | | | | | |

1. Reverse recovery condition $I_F=0.5A$, $I_R=1.0A$, Irr=0.25A.

2.Measured at 1.0 MHz and applied voltage of $4.0V_{dc}$

3. Thermal rSFistance from junction to terminal mounted on 5x5mm copper pad area

http://www.sse-diode.com